

isc Silicon NPN Power Transistor

ISC184

DESCRIPTION

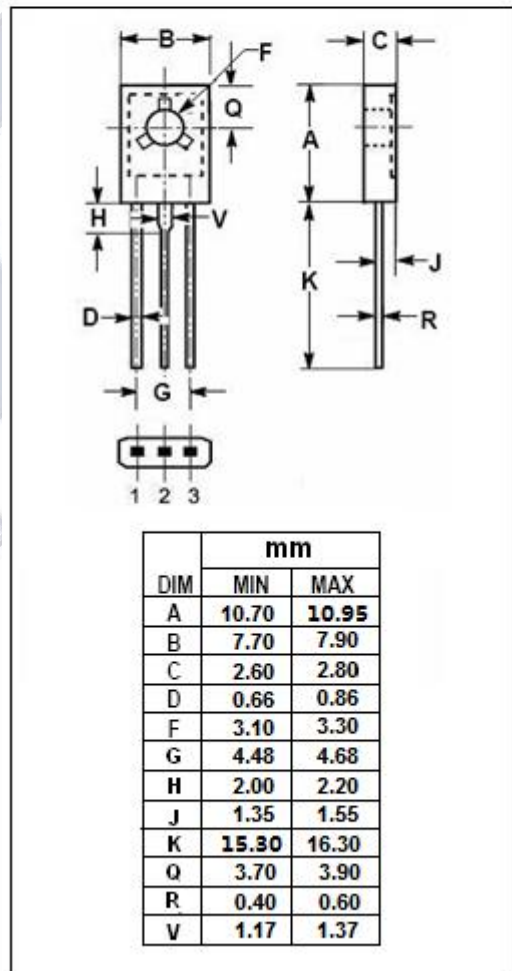
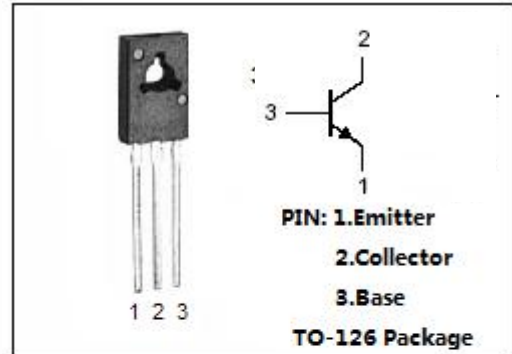
- High Collector Current- $I_C = 4A$
- Good Linearity of h_{FE}
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

- Suited for the output stage of audio amplifier, voltage regulator, DC-DC converter and relay driver.

ABSOLUTE MAXIMUM RATINGS ($T_a = 25^\circ C$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	80	V
V_{CEO}	Collector-Emitter Voltage	80	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current-Continuous	4	A
P_C	Collector Power Dissipation @ $T_C = 25^\circ C$	40	W
T_J	Junction Temperature	-65~150	$^\circ C$
T_{stg}	Storage Temperature Range	-65~150	$^\circ C$



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ELECTRICAL CHARACTERISTICS

T_C=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CE(sat)-1}	Collector-Emitter Saturation Voltage	I _C = 1.5 A; I _B = 0.15A			0.6	V
V _{BE(sat)-2}	Collector-Emitter Saturation Voltage	I _C = 4A; I _B = 1A			1.4	V
V _{BE(on)}	Base-Emitter On Voltage	I _C = 1.5A; V _{CE} = 2V			1.2	V
I _{CBO}	Collector Cutoff Current	V _{CB} =80V; I _E = 0			0.1	mA
I _{EBO}	Emitter Cutoff Current	V _{EB} = 5V; I _C = 0			1.0	mA
h _{FE-1}	DC Current Gain	I _C = 1.5A ; V _{CE} = 2V	20		80	
h _{FE-2}	DC Current Gain	I _C = 4A ; V _{CE} = 2V	7			